

## KSP8098/8099

## **Amplifier Transistor**

- Collector-Emitter Voltage: V<sub>CEO</sub>= KSP8098: 60V KSP8099: 80V
- Collector Power Dissipation: P<sub>C</sub> (max)=625mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



### 1. Emitter 2. Base 3. Collector

# **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: KSP8098	60	V
	: KSP8099	80	V
V <sub>CEO</sub> Collector-Emitter Voltage			
	: KSP8098	60	V
	: KSP8099	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	500	mA
P <sub>C</sub>	Collector Power Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage : KSP8098	I <sub>C</sub> =100μA, I <sub>E</sub> =0	60 80		V
BV <sub>CEO</sub>	: KSP8099  * Collector-Emitter Breakdown Voltage : KSP8098	I <sub>C</sub> =10mA, I <sub>B</sub> =0	60		V
	: KSP8099		80		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_{E}=10\mu A, I_{C}=0$	6		V
I <sub>CBO</sub>	Collector Cut-off Current : KSP8098 : KSP8099	V <sub>CB</sub> =60V, I <sub>E</sub> =0 V <sub>CB</sub> =80V, I <sub>E</sub> =0		100 100	nA nA
I <sub>CEO</sub>	Collector Cut-off Current	V <sub>CE</sub> =60V, I <sub>B</sub> =0		100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =6V, $I_{C}$ =0		100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA V <sub>CE</sub> =5V, I <sub>C</sub> =10mA V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	100 100 75	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA I <sub>C</sub> =100mA, I <sub>B</sub> =10mA		0.4 0.3	V V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage : KSP8098 : KSP8099	$V_{CE}$ =5V, $I_{C}$ =1mA $V_{CE}$ =5V, $I_{C}$ =10mA	0.5 0.6	0.7 0.8	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA f=100MHz	150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =5V, I <sub>E</sub> =0 f=1MHz		6	pF

\* Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

# **Typical Characteristics**

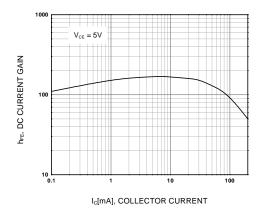


Figure 1. DC current Gain

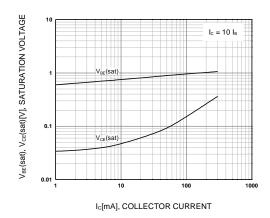


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

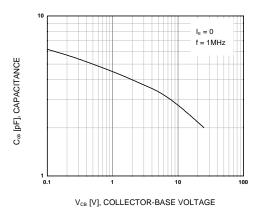


Figure 3. Output Capacitance

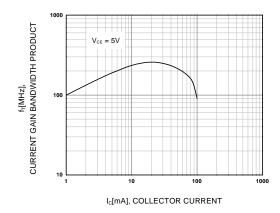
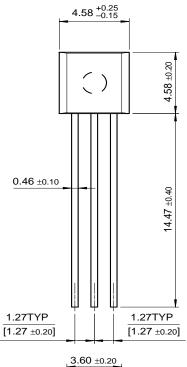
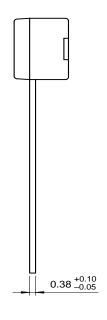
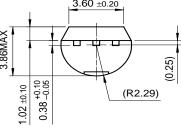


Figure 4. Current Gain Bandwidth Product

TO-92







Dimensions in Millimeters

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